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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	341
Number of Gates	300000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe3000l-1fg484i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

During Flash*Freeze Mode

- PLLs are turned off during Flash*Freeze mode.
- I/O pads are configured according to Table 2-5 on page 28 and Table 2-6 on page 29.
- Inputs and input clocks to the FPGA can toggle without any impact on static power consumption, assuming weak pull-up or pull-down is not selected.
- If weak pull-up or pull-down is selected and the input is driven to the opposite direction, power dissipation will occur.
- Any toggling signals will be charging and discharging the package pin capacitance.
- IGLOO and ProASIC3L outputs will be tristated unless the I/O is configured with weak pull-up or pull-down. The output of the I/O to the FPGA core is logic High regardless of whether the I/O pin is configured with a weak pull-up or pull-down. Refer to Table 2-5 on page 28 for more information.
- IGLOO nano and IGLOO PLUS output behavior will be based on the configuration defined by the user. Refer to Table 2-6 on page 29 for a description of output behavior during Flash*Freeze mode.
- The JTAG circuit is active; however, JTAG operations, such as JTAG commands, JTAG bypass, programming, and authentication, cannot be executed. The device must exit Flash*Freeze mode before JTAG commands can be sent. TCK should be static to avoid extra power consumption from the JTAG state machine.
- The FF pin must be externally asserted for the device to stay in Flash*Freeze mode.
- The FF pin is still active; i.e., the pin is used to exit Flash*Freeze mode when deasserted.

Exiting Flash*Freeze Mode

I/Os and Globals

- While exiting Flash*Freeze mode, inputs and globals will exit their Flash*Freeze state asynchronously to each other. As a result, clock and data glitches and narrow pulses may be generated while exiting Flash*Freeze mode, unless clock gating schemes are used.
- I/O banks are not all activated simultaneously when exiting Flash*Freeze mode. This can cause clocks and inputs to become enabled at different times, resulting in unexpected data being captured.
- Upon exiting Flash*Freeze mode, inputs and globals will no longer be tied High internally (does not apply to input hold state on IGLOO nano and IGLOO PLUS). If any of these signals are driven Low or tied Low externally, they will experience a High-to-Low transition internally when exiting Flash*Freeze mode.
- Applies only to IGLOO nano and IGLOO PLUS: Output hold state is asynchronously controlled by the signal driving the output buffer (output signal). This ensures a clean, glitch-free transition from hold state to output drive. However, any glitches on the output signal during exit from Flash*Freeze mode may result in glitches on the output pad.
- The above situations can cause glitches or invalid data to be clocked into and preserved in the device. Refer to the "Flash*Freeze Design Guide" on page 34 for solutions.

PLLs

• If the embedded PLL is used, the design must allow maximum acquisition time (per device datasheet) for the PLL to acquire the lock signal.

Flash*Freeze Pin Locations

Refer to the Pin Descriptions and Packaging chapter of specific device datasheets for information regarding Flash*Freeze pin location on the available packages. The Flash*Freeze pin location is independent of the device, allowing migration to larger or smaller devices while maintaining the same pin location on the board.

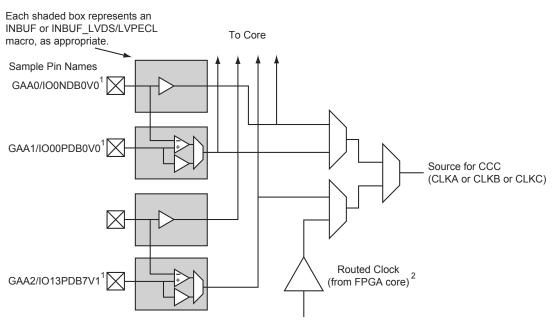
ProASIC3L FPGA Fabric User's Guide

Date	Changes			
51900147-2/5.07	In the following sentence, located in the "Flash*Freeze Mode" section, the bold text was changed from active high to active Low.	24		
	The Flash*Freeze pin (active low) is a dedicated pin used to enter or exit Flash*Freeze mode directly, or alternatively the pin can be routed internally to the FPGA core to allow the user's logic to decide if it is safe to transition to this mode.			
	Figure 2-2 • Flash*Freeze Mode Type 1 – Timing Diagram was updated.	25		
	Information about ULSICC was added to the "Prototyping for IGLOO and ProASIC3L Devices Using ProASIC3" section.	2-21		
51900147-1/3.07	In the "Flash*Freeze Mode" section, "active high" was changed to "active low."	24		
	The "Prototyping for IGLOO and ProASIC3L Devices Using ProASIC3" section was updated with information concerning the Flash*Freeze pin.	2-21		

Global Resources in Low Power Flash Devices

Figure 3-5 shows more detailed global input connections. It shows the global input pins connection to the northwest quadrant global networks. Each global buffer, as well as the PLL reference clock, can be driven from one of the following:

- 3 dedicated single-ended I/Os using a hardwired connection
- 2 dedicated differential I/Os using a hardwired connection (not supported for IGLOO nano or ProASIC3 nano devices)
- The FPGA core



GAA[0:2]: GA represents global in the northwest corner of the device. A[0:2]: designates specific A clock source.

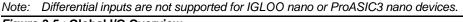


Figure 3-5 • Global I/O Overview

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DYNCCC Core(.CLKA(CLKA), .EXTFB(GND), .POWERDOWN(POWERDOWN), .GLA(GLA), .LOCK(LOCK), .CLKB(CLKB), .GLB(GLB), .YB(), .CLKC(CLKC), .GLC(GLC), .YC(), .SDIN(SDIN), .SCLK(SCLK), .SSHIFT(SSHIFT), .SUPDATE(SUPDATE), .MODE(MODE), .SDOUT(SDOUT), .OADIV0(GND), .OADIV1(GND), .OADIV2(VCC), .OADIV3(GND), .OADIV4(GND), .OAMUX0(GND), .OAMUX1(GND), .OAMUX2(VCC), .DLYGLA0(GND), .DLYGLA1(GND), .DLYGLA2(GND), .DLYGLA3(GND), .DLYGLA4(GND), .OBDIV0(GND), .OBDIV1(GND), .OBDIV2(GND), .OBDIV3(GND), .OBDIV4(GND), .OBMUX0(GND), .OBMUX1(GND), .OBMUX2(GND), .DLYYB0(GND), .DLYYB1(GND), .DLYYB2(GND), .DLYYB3(GND), .DLYYB4(GND), .DLYGLB0(GND), .DLYGLB1(GND), .DLYGLB2(GND), .DLYGLB3(GND), .DLYGLB4(GND), .OCDIV0(GND), .OCDIV1(GND), .OCDIV2(GND), .OCDIV3(GND), .OCDIV4(GND), .OCMUX0(GND), .OCMUX1(GND), .OCMUX2(GND), .DLYYC0(GND), .DLYYC1(GND), .DLYYC2(GND), .DLYYC3(GND), .DLYYC4(GND), .DLYGLC0(GND), .DLYGLC1(GND), .DLYGLC2(GND), .DLYGLC3(GND), .DLYGLC4(GND), .FINDIV0(VCC), .FINDIV1(GND), .FINDIV2(VCC), .FINDIV3(GND), .FINDIV4(GND), .FINDIV5(GND), .FINDIV6(GND), .FBDIV0(GND), .FBDIV1(GND), .FBDIV2(GND), .FBDIV3(GND), .FBDIV4(GND), .FBDIV5(VCC), .FBDIV6(GND), .FBDLY0(GND), .FBDLY1(GND), .FBDLY2(GND), .FBDLY3(GND), .FBDLY4(GND), .FBSEL0(VCC), .FBSEL1(GND), .XDLYSEL(GND), .VCOSEL0(GND), .VCOSEL1(GND), .VCOSEL2(VCC)); defparam Core.VCOFREQUENCY = 165.000;

endmodule

Delayed Clock Configuration

The CLKDLY macro can be generated with the desired delay and input clock source (Hardwired I/O, External I/O, or Core Logic), as in Figure 4-28.

Figure 4-28 • Delayed Clock Configuration Dialog Box

After setting all the required parameters, users can generate one or more PLL configurations with HDL or EDIF descriptions by clicking the **Generate** button. SmartGen gives the option of saving session results and messages in a log file:

```
Macro Parameters
*****
                               : delay_macro
Name
Family
                               : ProASIC3
                               : Verilog
Output Format
                               : Delayed Clock
Type
Delay Index
                               : 2
CLKA Source
                               : Hardwired I/O
Total Clock Delay = 0.935 ns.
The resultant CLKDLY macro Verilog netlist is as follows:
module delay_macro(GL,CLK);
output GL;
input CLK;
```

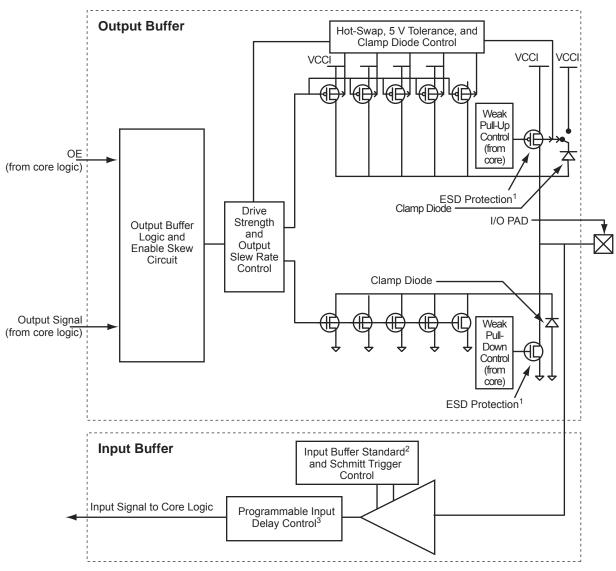
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Date	Changes	Page	
v1.2 (June 2008)	 The following changes were made to the family descriptions in Figure 4-1 • Overview of the CCCs Offered in Fusion, IGLOO, and ProASIC3: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six. 	77	
v1.1 (March 2008)	Table 4-1 • Flash-Based FPGAs and the associated text were updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	79	
	The "Global Input Selections" section was updated to include 15 k gate devices as supported I/O types for globals, for CCC only.	87	
	Table 4-5 • Number of CCCs by Device Size and Package was revised to include ProASIC3L, IGLOO PLUS, A3P015, AGL015, AGLP030, AGLP060, and AGLP125.	94	
	The "IGLOO and ProASIC3 CCC Locations" section was revised to include 15 k gate devices in the exception statements, as they do not contain PLLs.	97	
v1.0 (January 2008)	Information about unlocking the PLL was removed from the "Dynamic PLL Configuration" section.	103	
	In the "Dynamic PLL Configuration" section, information was added about running Layout and determining the exact setting of the ports.	116	
	In Table 4-8 • Configuration Bit Descriptions for the CCC Blocks, the following bits were updated to delete "transport to the user" and reference the footnote at the bottom of the table: 79 to 71.	106	

I/O Structures in IGLOO and ProASIC3 Devices

	Maximum Performance						
Specification	ProASIC3	IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage	IGLOO V2, 1.2 V DC Core Supply Voltage				
LVTTL/LVCMOS 3.3 V	200 MHz	180 MHz	TBD				
LVCMOS 2.5 V	250 MHz	230 MHz	TBD				
LVCMOS 1.8 V	200 MHz	180 MHz	TBD				
LVCMOS 1.5 V	130 MHz	120 MHz	TBD				
PCI	200 MHz	180 MHz	TBD				
PCI-X	200 MHz	180 MHz	TBD				
LVDS	350 MHz	300 MHz	TBD				
LVPECL	350 MHz	300 MHz	TBD				

Table 7-6 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in IGLOO and ProASIC Devices (maximum drive strength and high slew selected)



Notes:

- 1. All NMOS transistors connected to the I/O pad serve as ESD protection.
- 2. See Table 7-2 on page 177 for available I/O standards.

3. Programmable input delay is applicable only to ProASIC3EL and RT ProASIC3 devices.

Figure 7-4 • Simplified I/O Buffer Circuitry

I/O Registers

Each I/O module contains several input, output, and enable registers. Refer to Figure 7-4 for a simplified representation of the I/O block. The number of input registers is selected by a set of switches (not shown in Figure 7-2 on page 181) between registers to implement single-ended or differential data transmission to and from the FPGA core. The Designer software sets these switches for the user. A common CLR/PRE signal is employed by all I/O registers when I/O register combining is used. Input Register 2 does not have a CLR/PRE pin, as this register is used for DDR implementation. The I/O register combining must satisfy certain rules.

IGLOO and ProASIC3

For boards and cards with three levels of staging, card power supplies must have time to reach their final values before the I/Os are connected. Pay attention to the sizing of power supply decoupling capacitors on the card to ensure that the power supplies are not overloaded with capacitance.

Cards with three levels of staging should have the following sequence:

- Grounds
- Powers
- I/Os and other pins

For Level 3 and Level 4 compliance with the 30K gate device, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

Cold-Sparing Support

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 μ s.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

The 30 k gate devices fully support cold-sparing, since the I/O clamp diode is always off (see Table 7-12 on page 193). If the 30 k gate device is used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the 30K gate devices do not have built-in I/O clamp diodes.

For other IGLOO and ProASIC3 devices, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each I/O pin to 0 V. If the resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitance is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

IGLOOe and ProASIC3E devices support cold-sparing for all I/O configurations. Standards, such as PCI, that require I/O clamp diodes can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 k Ω , and the resulting current is equal to 3.3 V / 45 k Ω = 73 µA for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input LOW when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

Table 7-19 shows some high-level interfacing examples using low power flash devices.

	(Clock	I/O						
Interface	Туре	Frequency	Туре	Signals In	Signals Out	Data I/O			
GM	Src Sync	125 MHz	LVTTL	8	8	125 Mbps			
ТВІ	Src Sync	125 MHz	LVTTL	10	10	125 Mbps			
XSBI	Src Sync	644 MHz	LVDS	16	16	644 Mbps			
XGMI	Src Sync DDR	156 MHz	HSTL1	32	32	312 Mbps			
FlexBus 3	Sys Sync	104 MHz	LVTTL	≤ 32	≤ 32	≤ 104			
Pos-PHY3/SPI-3	Sys Sync	104	LVTTL	8, 16, 32	8, 16, 32	\leq 104 Mbps			
FlexBus 4/SPI-4.1	Src Sync	200 MHz	HSTL1	16,64	16,64	200 Mbps			
Pos-PHY4/SPI-4.2	Src Sync DDR	≥ 311 MHz	LVDS	16	16	\geq 622 Mbps			
SFI-4.1	Src Sync	622 MHz	LVDS	16	16	622 Mbps			
CSIX L1	Sys Sync	\leq 250 MHz	HSTL1	32,64,96,128	32,64,96,128	\leq 250 Mbps			
Hyper Transport	Sys Sync DDR	\leq 800 MHz	LVDS	2,4,8,16	2,4,8,16	\leq 1.6 Gbps			
Rapid I/O Parallel	Sys Sync DDR	250 MHz – 1 GHz	LVDS	8,16	8,16	\leq 2 Gbps			
Star Fabric	CDR		LVDS	4	4	622 Mbps			

Table 7-19 • High-Level Interface Examples

Note: Sys Sync = System Synchronous Clocking, Src Sync = Source Synchronous Clocking, and CDR = Clock and Data Recovery.

Conclusion

IGLOO and ProASIC3 support for multiple I/O standards minimizes board-level components and makes possible a wide variety of applications. The Microsemi Designer software, integrated with Libero SoC, presents a clear visual display of I/O assignments, allowing users to verify I/O and board-level design requirements before programming the device. The IGLOO and ProASIC3 device I/O features and functionalities ensure board designers can produce low-cost and low power FPGA applications fulfilling the complexities of contemporary design needs.

I/O Register Combining

Every I/O has several embedded registers in the I/O tile that are close to the I/O pads. Rather than using the internal register from the core, the user has the option of using these registers for faster clock-to-out timing, and external hold and setup. When combining these registers at the I/O buffer, some architectural rules must be met. Provided these rules are met, the user can enable register combining globally during Compile (as shown in the "Compiling the Design" section on page 261).

This feature is supported by all I/O standards.

Rules for Registered I/O Function

- 1. The fanout between an I/O pin (D, Y, or E) and a register must be equal to one for combining to be considered on that pin.
- 2. All registers (Input, Output, and Output Enable) connected to an I/O must share the same clear or preset function:
 - If one of the registers has a CLR pin, all the other registers that are candidates for combining in the I/O must have a CLR pin.
 - If one of the registers has a PRE pin, all the other registers that are candidates for combining in the I/O must have a PRE pin.
 - If one of the registers has neither a CLR nor a PRE pin, all the other registers that are candidates for combining must have neither a CLR nor a PRE pin.
 - If the clear or preset pins are present, they must have the same polarity.
 - If the clear or preset pins are present, they must be driven by the same signal (net).
- 3. Registers connected to an I/O on the Output and Output Enable pins must have the same clock and enable function:
 - Both the Output and Output Enable registers must have an E pin (clock enable), or none at all.
 - If the E pins are present, they must have the same polarity. The CLK pins must also have the same polarity.

In some cases, the user may want registers to be combined with the input of a bibuf while maintaining the output as-is. This can be achieved by using PDC commands as follows:

```
set_io <signal name> -REGISTER yes -----register will combine
set_preserve <signal name> ----register will not combine
```

Weak Pull-Up and Weak Pull-Down Resistors

When the I/O is pulled up, it is connected to the VCCI of its corresponding I/O bank. When it is pulled down, it is connected to GND. Refer to the datasheet for more information.

For low power applications, configuration of the pull-up or pull-down of the I/O can be used to set the I/O to a known state while the device is in Flash*Freeze mode. Refer to the "Flash*Freeze Technology and Low Power Modes in IGLOO and ProASIC3L Devices" chapter in the *IGLOOe FPGA Fabric User's Guide* or *ProASIC3E FPGA Fabric User's Guide* for more information.

The Flash*Freeze (FF) pin cannot be configured with a weak pull-down or pull-up I/O attribute, as the signal needs to be driven at all times.

Output Slew Rate Control

The slew rate is the amount of time an input signal takes to get from logic LOW to logic HIGH or vice versa.

It is commonly defined as the propagation delay between 10% and 90% of the signal's voltage swing. Slew rate control is available for the output buffers of low power flash devices. The output buffer has a programmable slew rate for both HIGH-to-LOW and LOW-to-HIGH transitions. Slew rate control is available for LVTTL, LVCMOS, and PCI-X I/O standards. The other I/O standards have a preset slew value.

The slew rate can be implemented by using a PDC command (Table 8-6 on page 218), setting it "High" or "Low" in the I/O Attribute Editor in Designer, or instantiating a special I/O macro. The default slew rate value is "High."

I/O Structures in IGLOOe and ProASIC3E Devices

I/O Software Support

In Libero SoC software, default settings have been defined for the various I/O standards supported. Changes can be made to the default settings via the use of attributes; however, not all I/O attributes are applicable for all I/O standards. Table 8-16 lists the valid I/O attributes that can be manipulated by the user for each I/O standard.

Single-ended I/O standards in low power flash devices support up to five different drive strengths.

Table 8-16 • IGLOOe and ProASIC3E I/O Attributes vs. I/O Standard Applications

I/O Standard LVTTL/LVCMOS 3.3 V	SLEW (output only)	<	SKEW (all macros with OE)	RES_PULL	 OUT_LOAD (output only) 		< IN_DELAY (input only)	< IN_DELAY_VAL (input only)	SCHMITT_TRIGGER (input only)	< HOT_SWAPPABLE
LVCMOS 2.5 V	✓ ✓	✓ ✓	✓ ✓	✓ ✓	✓ ✓	✓ ✓	✓ ✓	✓ ✓	✓ ✓	✓ ✓
LVCMOS 2.5/5.0 V	✓ ✓	✓ ✓	✓ ✓	✓ ✓	▼ ✓	✓ ✓	▼ ✓	✓ ✓	▼ ✓	✓ ✓
LVCMOS 1.8 V	✓ ✓	✓ ✓	✓ ✓	✓ ✓	▼ ✓	✓ ✓	▼ ✓	✓ ✓	✓ ✓	✓ ✓
LVCMOS 1.5 V	✓ ✓	▼ ✓	✓ ✓	▼ ✓	▼ ✓	▼ ✓	✓ ✓	✓ ✓	▼ ✓	✓ ✓
PCI (3.3 V)	v	v	✓ ✓	v	▼ ✓	✓ ✓	▼ ✓	✓ ✓	v	v
PCI-X (3.3 V)	~		✓ ✓		✓ ✓	✓ ✓	✓ ✓	✓ ✓		
	✓				-	-				
GTL+ (3.3 V)			<i>✓</i>		1	<i>✓</i>	1	1		1
GTL+ (2.5 V)			1		1	✓	1	1		✓
GTL (3.3 V)			~		~	✓	✓	~		✓
GTL (2.5 V)			<i>✓</i>		✓	✓	1	~		✓
HSTL Class I			✓		✓	✓	✓	✓		✓
HSTL Class II			✓		1	✓	1	1		✓
SSTL2 Class I and II			✓		✓	✓	✓	✓		✓
SSTL3 Class I and II			1		1	1	1	1		✓
LVDS, B-LVDS, M- LVDS			1			~	~	~		1
LVPECL						✓	1	1		✓

Table 8-17 on page 243 lists the default values for the above selectable I/O attributes as well as those that are preset for each I/O standard.

I/O Structures in IGLOOe and ProASIC3E Devices

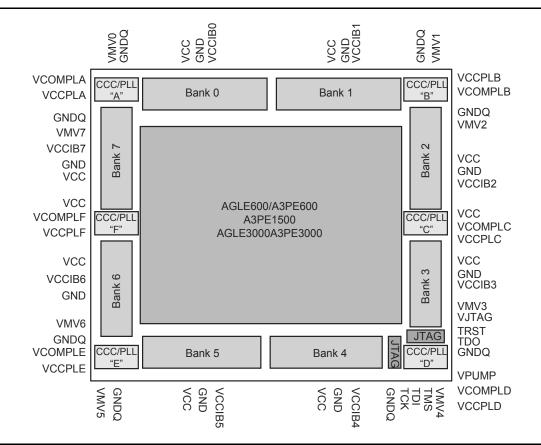


Figure 8-20 • User I/O Naming Conventions of IGLOOe and ProASIC3E Devices – Top View

Board-Level Considerations

Low power flash devices have robust I/O features that can help in reducing board-level components. The devices offer single-chip solutions, which makes the board layout simpler and more immune to signal integrity issues. Although, in many cases, these devices resolve board-level issues, special attention should always be given to overall signal integrity. This section covers important board-level considerations to facilitate optimum device performance.

Termination

Proper termination of all signals is essential for good signal quality. Nonterminated signals, especially clock signals, can cause malfunctioning of the device.

For general termination guidelines, refer to the *Board-Level Considerations* application note for Microsemi FPGAs. Also refer to the "Pin Descriptions" chapter of the appropriate datasheet for termination requirements for specific pins.

Low power flash I/Os are equipped with on-chip pull-up/-down resistors. The user can enable these resistors by instantiating them either in the top level of the design (refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide* for the available I/O macros with pull-up/-down) or in the I/O Attribute Editor in Designer if generic input or output buffers are instantiated in the top level. Unused I/O pins are configured as inputs with pull-up resistors.

As mentioned earlier, low power flash devices have multiple programmable drive strengths, and the user can eliminate unwanted overshoot and undershoot by adjusting the drive strengths.

I/O Software Control in Low Power Flash Devices

Flash FPGAs I/O Support

The flash FPGAs listed in Table 9-1 support I/Os and the functions described in this document.

Table 9-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 9-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 9-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.



DDR for Microsemi's Low Power Flash Devices

Instantiating DDR Registers

Using SmartGen is the simplest way to generate the appropriate RTL files for use in the design. Figure 10-4 shows an example of using SmartGen to generate a DDR SSTL2 Class I input register. SmartGen provides the capability to generate all of the DDR I/O cells as described. The user, through the graphical user interface, can select from among the many supported I/O standards. The output formats supported are Verilog, VHDL, and EDIF.

Figure 10-5 on page 277 through Figure 10-8 on page 280 show the I/O cell configured for DDR using SSTL2 Class I technology. For each I/O standard, the I/O pad is buffered by a special primitive that indicates the I/O standard type.

Figure 10-4 • Example of Using SmartGen to Generate a DDR SSTL2 Class I Input Register

11 – Programming Flash Devices

Introduction

This document provides an overview of the various programming options available for the Microsemi flash families. The electronic version of this document includes active links to all programming resources, which are available at http://www.microsemi.com/soc/products/hardware/default.aspx. For Microsemi antifuse devices, refer to the *Programming Antifuse Devices* document.

Summary of Programming Support

FlashPro4 and FlashPro3 are high-performance in-system programming (ISP) tools targeted at the latest generation of low power flash devices offered by the SmartFusion,[®] Fusion, IGLOO,[®] and ProASIC[®]3 families, including ARM-enabled devices. FlashPro4 and FlashPro3 offer extremely high performance through the use of USB 2.0, are high-speed compliant for full use of the 480 Mbps bandwidth, and can program ProASIC3 devices in under 30 seconds. Powered exclusively via USB, FlashPro4 and FlashPro3 provide a VPUMP voltage of 3.3 V for programming these devices.

FlashPro4 replaced FlashPro3 in 2010. FlashPro4 supports SmartFusion, Fusion, ProASIC3, and IGLOO devices as well as future generation flash devices. FlashPro4 also adds 1.2 V programming for IGLOO nano V2 devices. FlashPro4 is compatible with FlashPro3; however it adds a programming mode (PROG_MODE) signal to the previously unused pin 4 of the JTAG connector. The PROG_MODE goes high during programming and can be used to turn on a 1.5 V external supply for those devices that require 1.5 V for programming. If both FlashPro3 and FlashPro4 programmers are used for programming the same boards, pin 4 of the JTAG connector must not be connected to anything on the board because FlashPro4 uses pin 4 for PROG_MODE.

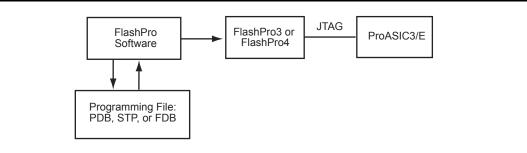


Figure 11-1 • FlashPro Programming Setup

General Flash Programming Information

Programming Basics

When choosing a programming solution, there are a number of options available. This section provides a brief overview of those options. The next sections provide more detail on those options as they apply to Microsemi FPGAs.

Reprogrammable or One-Time-Programmable (OTP)

Depending on the technology chosen, devices may be reprogrammable or one-time-programmable. As the name implies, a reprogrammable device can be programmed many times. Generally, the contents of such a device will be completely overwritten when it is reprogrammed. All Microsemi flash devices are reprogrammable.

An OTP device is programmable one time only. Once programmed, no more changes can be made to the contents. Microsemi flash devices provide the option of disabling the reprogrammability for security purposes. This combines the convenience of reprogrammability during design verification with the security of an OTP technology for highly sensitive designs.

Device Programmer or In-System Programming

There are two fundamental ways to program an FPGA: using a device programmer or, if the technology permits, using in-system programming. A device programmer is a piece of equipment in a lab or on the production floor that is used for programming FPGA devices. The devices are placed into a socket mounted in a programming adapter module, and the appropriate electrical interface is applied. The programmed device can then be placed on the board. A typical programmer, used during development, programs a single device at a time and is referred to as a single-site engineering programmer.

With ISP, the device is already mounted onto the system printed circuit board when programming occurs. Typically, ISD programming is performed via a JTAG interface on the FPGA. The JTAG pins can be controlled either by an on-board resource, such as a microprocessor, or by an off-board programmer through a header connection. Once mounted, it can be programmed repeatedly and erased. If the application requires it, the system can be designed to reprogram itself using a microprocessor, without the use of any external programmer.

If multiple devices need to be programmed with the same program, various multi-site programming hardware is available in order to program many devices in parallel. Microsemi In House Programming is also available for this purpose.

Programming Features for Microsemi Devices

Flash Devices

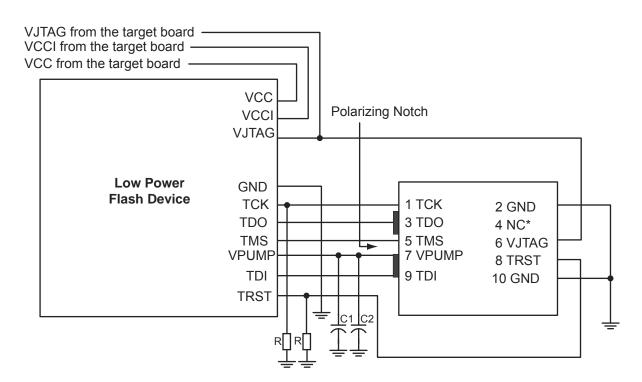
The flash devices supplied by Microsemi are reprogrammable by either a generic device programmer or ISP. Microsemi supports ISP using JTAG, which is supported by the FlashPro4 and FlashPro3, FlashPro Lite, Silicon Sculptor 3, and Silicon Sculptor II programmers.

Levels of ISP support vary depending on the device chosen:

- All SmartFusion, Fusion, IGLOO, and ProASIC3 devices support ISP.
- IGLOO, IGLOOe, IGLOO nano V5, and IGLOO PLUS devices can be programmed in-system when the device is using a 1.5 V supply voltage to the FPGA core.
- IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only) or 1.5 V. IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.

Board-Level Considerations

A bypass capacitor is required from VPUMP to GND for all low power flash devices during programming. This bypass capacitor protects the devices from voltage spikes that may occur on the VPUMP supplies during the erase and programming cycles. Refer to the "Pin Descriptions and Packaging" chapter of the appropriate device datasheet for specific recommendations. For proper programming, 0.01 μ F and 0.33 μ F capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible. The bypass capacitor must be placed within 2.5 cm of the device pins.



Note: *NC (FlashPro3/3X); Prog_Mode (FlashPro4). Prog_Mode on FlashPro4 is an output signal that goes High during device programming and returns to Low when programming is complete. This signal can be used to drive a system to provide a 1.5 V programming signal to IGLOO nano, ProASIC3L, and RT ProASIC3 devices that can run with 1.2 V core voltage but require 1.5 V for programming. IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only), but IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.

Figure 13-6 • Board Layout and Programming Header Top View

Troubleshooting Signal Integrity

Symptoms of a Signal Integrity Problem

A signal integrity problem can manifest itself in many ways. The problem may show up as extra or dropped bits during serial communication, changing the meaning of the communication. There is a normal variation of threshold voltage and frequency response between parts even from the same lot. Because of this, the effects of signal integrity may not always affect different devices on the same board in the same way. Sometimes, replacing a device appears to make signal integrity problems go away, but this is just masking the problem. Different parts on identical boards will exhibit the same problem sooner or later. It is important to fix signal integrity problems early. Unless the signal integrity problems are severe enough to completely block all communication between the device and the programmer, they may show up as subtle problems. Some of the FlashPro4/3/3X exit codes that are caused by signal integrity problems are not the only possible cause of these

Power-Up/-Down Behavior of Low Power Flash Devices

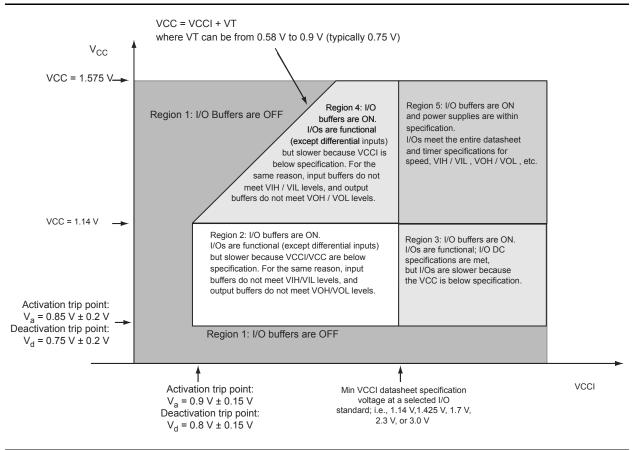


Figure 18-5 • I/O State as a Function of VCCI and VCC Voltage Levels for IGLOO V2, IGLOO nano V2, IGLOO PLUS V2, and ProASIC3L Devices Running at VCC = 1.2 V ± 0.06 V

B – **Product Support**

Microsemi SoC Products Group backs its products with various support services, including Customer Service, Customer Technical Support Center, a website, electronic mail, and worldwide sales offices. This appendix contains information about contacting Microsemi SoC Products Group and using these support services.

Customer Service

Contact Customer Service for non-technical product support, such as product pricing, product upgrades, update information, order status, and authorization.

From North America, call 800.262.1060 From the rest of the world, call 650.318.4460 Fax, from anywhere in the world, 650.318.8044

Customer Technical Support Center

Microsemi SoC Products Group staffs its Customer Technical Support Center with highly skilled engineers who can help answer your hardware, software, and design questions about Microsemi SoC Products. The Customer Technical Support Center spends a great deal of time creating application notes, answers to common design cycle questions, documentation of known issues, and various FAQs. So, before you contact us, please visit our online resources. It is very likely we have already answered your questions.

Technical Support

Visit the Customer Support website (www.microsemi.com/soc/support/search/default.aspx) for more information and support. Many answers available on the searchable web resource include diagrams, illustrations, and links to other resources on the website.

Website

You can browse a variety of technical and non-technical information on the SoC home page, at www.microsemi.com/soc.

Contacting the Customer Technical Support Center

Highly skilled engineers staff the Technical Support Center. The Technical Support Center can be contacted by email or through the Microsemi SoC Products Group website.

Email

You can communicate your technical questions to our email address and receive answers back by email, fax, or phone. Also, if you have design problems, you can email your design files to receive assistance. We constantly monitor the email account throughout the day. When sending your request to us, please be sure to include your full name, company name, and your contact information for efficient processing of your request.

The technical support email address is soc_tech@microsemi.com.

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